Plastic Infrared Emitting Diode

OP265WPS



Features:

- T-1 (3 mm) package style
- Broad irradiance pattern
- Point source with flat lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode



Description:

The **OP265WPS** point source model is a flat-lensed 850 nm diode with a broad radiation pattern that provides relatively even illumination over a large area. Its stable forward voltage (V_F) vs. temperature characteristic makes this device appropriate for applications where voltage is limited (such as battery operation), while the low rise time/fall time (t_r/t_f) makes it ideal for high-speed operation.

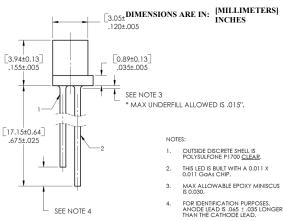
OP265 devices conform to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

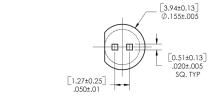
- Space-limited applications
- · Applications requiring coupling efficiency
- Precision optical designs
- Battery-operated or voltage-limited applications

Ordering Information								
Part Number	LED Peak Wavelength	Output Power (mW/cm²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length			
OP265WPS	850 nm	.055 / .55	20 / 50	120°	0.50"			





Pin#	LED	
1	Cathode	
2	Anode	



DISCRETE PIN-OUT

- 1 CATHODE
- 2 ANODE

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)	
Storage and Operating Temperature Range	-40° C to +100° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- 3. E_{E(APT)} is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E_{E(APT)} is not necessarily uniform within the measured area

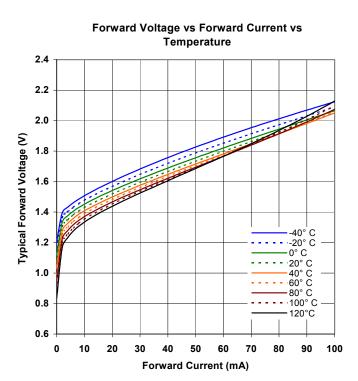
Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode							
E _{E (APT)}	Apertured Radiant Incidence	2.70	-	-	mW/cm ²	I _F = 20 mA ⁽³⁾	
V _F	Forward Voltage	-	-	1.80	V	I _F = 20 mA	
I _R	Reverse Current		-	20	μΑ	V _R = 2 V	
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 10 mA	
В	Spectral Bandwidth between Half Power Points	-	-	-	nm	I _F = 20 mA	

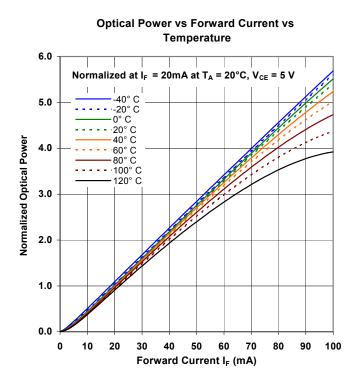
Plastic Infrared Emitting Diode

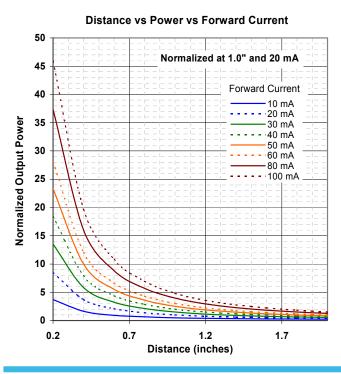
OP265WPS



Performance OP265WPS







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